T1

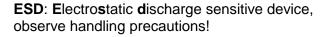


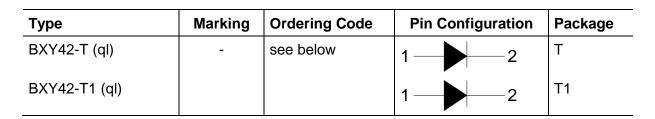
HiRel Silicon PIN Diode

- HiRel Discrete and Microwave Semiconductor
- PIN Diode for high speed switching of RF signals
- Very low capacitance
- Hermetically sealed microwave package

ESA/SCC Detail Spec. No.: 5513/017

Type Variant No.s 01 to 02





Т

(ql) Quality Level: P: Professional Quality

H: High Rel QualityS: Space Quality

ES: ESA Space Quality

(see order instructions for ordering example)



Maximum Ratings

Parameter	Symbol	Values	Unit
Reverse Voltage	V _R	50	V
Peak Forward Current 1)	I _{FM}	5	А
Power Dissipation	P _{tot}		mW
BXY42-T ²⁾		600	
BXY42-T1 ³⁾		350	
Operating Temperature Range	T _{op}	-55 to +175	°C
Storage Temperature Range	T _{stg}	-65 to +175	°C
Soldering Temperature 4)	T _{sol}	+250	°C
Junction Temperature	T _j	175	°C
Thermal Resistance Junction-Case	R _{th(j-c)}		K/W
BXY42-T		200	
BXY42-T1		350	

Notes.:

- 1.) At $t_p = 1.0 \mu s$, Duty Cycle=0.001%
- 2.) At $T_{CASE} = 55$ °C. For $T_{CASE} > 55$ °C derating is required.
- 3.) At $T_{CASE} = 52,5$ °C. For $T_{CASE} > 52,5$ °C derating is required. 4.) During 5 sec. maximum. The same terminal shall not be resoldered until 5 minutes have elapsed.

Electrical Characteristics

at T_A=25°C; unless otherwise specified

Parameter	Symbol		Values		Unit
		min.	typ.	max.	
DC Characteristics					
Reverse Current 1	I _{R1}	-	-	10	μΑ
V _{R1} =50V					
Reverse Current 2	I _{R2}	-	-	5	nA
V _{R2} =40V					
Forward Voltage	V _F	-	0,97	1,1	V
I _F =100mA					



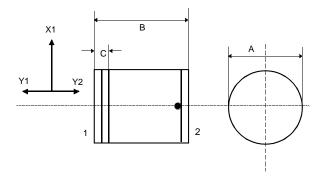


Electrical Characteristics (continued)

Parameter	Symbol	Values		Unit	
		min.	typ.	max.	
AC Characteristics					
Total Capacitance	Ст	-	0,22	0,24	pF
V _R =20V; f=1MHz					
Forward Resistance 1	R _{F1}	-	2	3,5	Ω
f=100MHz, I _{F1} =1mA					
Forward Resistance 2	R _{F2}	-	1	2,5	Ω
f=100MHz, I _{F2} =10mA					
Minority Carrier Lifetime		35	50	-	ns
$I_F=10mA$, $I_R=6mA$, $I_R=3mA$					

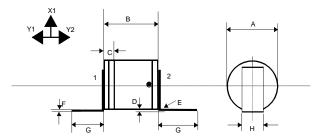


T Package



Symbol	Millimetre		
	min	max	
Α	1,30	1,45	
В	1,15	1,35	
С	-	0,40	

T1 Package



Symbol	Millimetre		
	min	max	
Α	1,30	1,45	
В	1,15	1,35	
С	ı	0,40	
D	0,10	0,50	
Е	-	0,30	
F	0,06	0,10	
G	5,50	-	
Н	0,40	0,60	



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